Electronic Supplementary Material (ESI) for Nanoscale.

Supporting Information

Quantum Spin Hall Insulators in Strain-modified Arsenene

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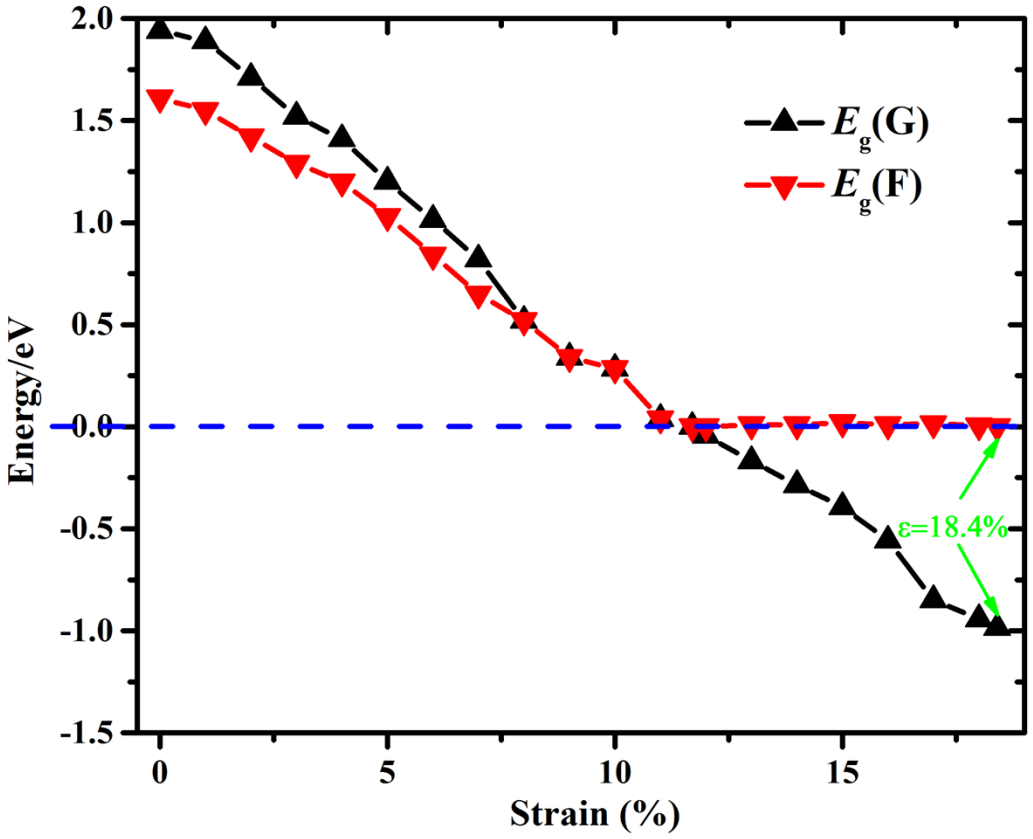

Figure S1 Strain dependent of functional energy gaps E_g (F) and band gaps at G point E_g (G).

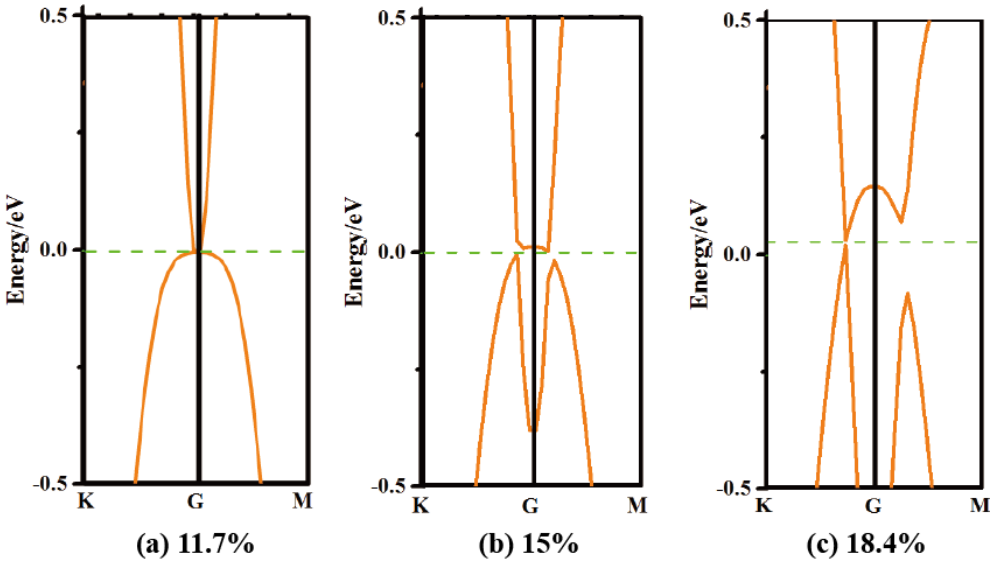

Figure S2 Enlarged band structures around Fermi level for arsenene with different strain. Green dashed lines represents Fermi level at 0 eV.

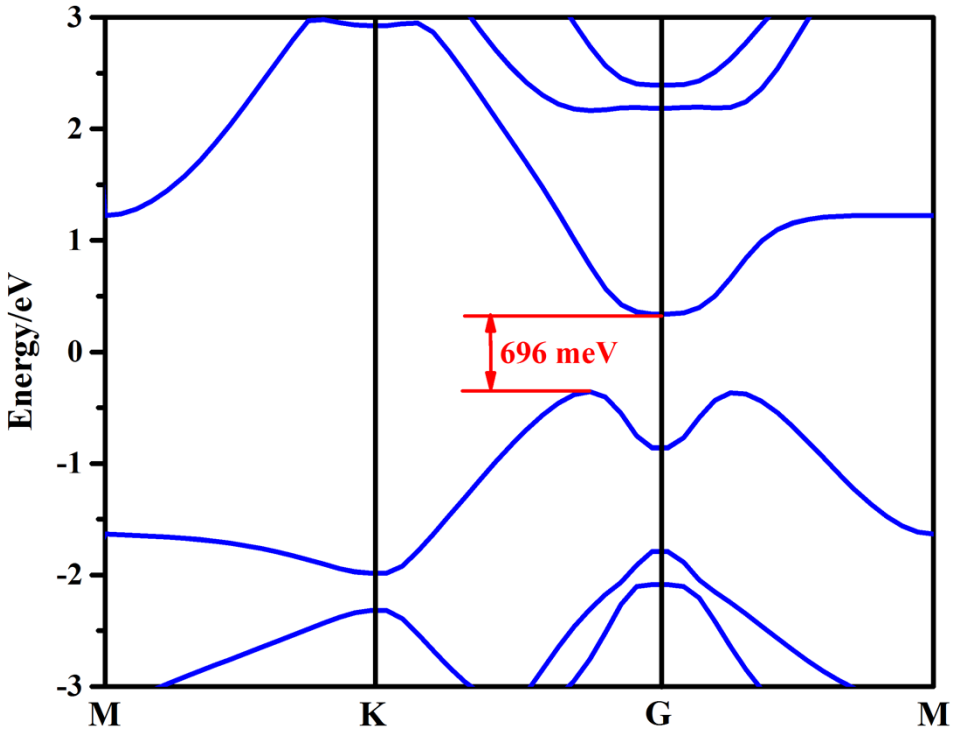

Figure S3 Band structure of arsenene under strain of 18.4%, calculated by HSE06 method with SOC effect.